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<p>(21) International Application Number: PCT/US98/21807 (22) International Filing Date: 14 October 1998 (14.10.98) (30) Priority Data: 60/062,856 14 October 1997 (14.10.97) US (71) Applicant (for all designated States except US): ADVANCED CHEMICAL SYSTEMS INTERNATIONAL, INC. [US/US]; 510 Alder Drive, Milpitas, CA 95035 (US). (72) Inventors; and (75) Inventors/Applicants (for US only): WOJTCZAK, William, A. [US/US]; 350 Elan Village Lane #1, San Jose, CA 95134 (US). GUAN, George [US/US]; 3900 Moorpark Avenue #58, San Jose, CA 95117 (US). (74) Agents: GUILLOT, Robert, O. et al.; Oppenheimer Wolff &amp; Donnelly LLP, Suite 400, 101 Park Center Plaza, San Jose, CA 95113 (US).</p>		<p>(81) Designated States: CA, ID, IL, JP, KR, SG, US, European patent (AT, BE, CH, CY, DE, DK, ES, FI, FR, GB, GR, IE, IT, LU, MC, NL, PT, SE).  <b>Published</b> <i>With international search report.</i></p>
<p>(54) Title: AMMONIUM BORATE CONTAINING COMPOSITIONS FOR STRIPPING RESIDUES FROM SEMICONDUCTOR SUBSTRATES</p> <p>(57) Abstract</p> <p>The present invention comprises formulations for stripping wafer residues which originate from a halogen based plasma metal etching followed by oxygen plasma ashing. The formulations contain the following general components (percentages are by weight): an organic amine or mixture of amines 15–60 %, water 20–60 %, ammonium tetraborate or ammonium pentaborate 9–20 %, an optional polar organic solvent 0–15 %.</p>		